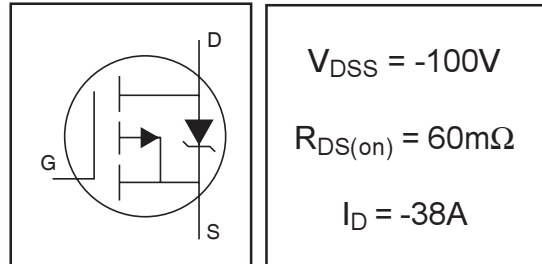


**IRF5210SPbF**  
**IRF5210LPbF**

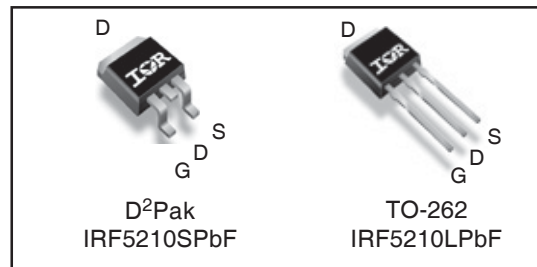
HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- 150°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to  $T_{jmax}$
- Some Parameters are Different from IRF5210S/L
- P-Channel
- Lead-Free



**Description**

Features of this design are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in a wide variety of other applications.



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-38	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-24	
$I_{DM}$	Pulsed Drain Current ①	-140	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation	3.1	W
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	170	
	Linear Derating Factor	1.3	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	120	mJ
$I_{AR}$	Avalanche Current ①	-23	A
$E_{AR}$	Repetitive Avalanche Energy ①	17	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-7.4	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state) ⑤	—	40	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-100	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.11	—	V/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	60	m $\Omega$	$V_{GS} = 10V, I_D = -38A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
gfs	Forward Transconductance	9.5	—	—	S	$V_{DS} = -50V, I_D = -23A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-50	$\mu A$	$V_{DS} = -100V, V_{GS} = 0V$ $V_{DS} = -80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$
$Q_g$	Total Gate Charge	—	150	230	nC	$I_D = -23A$
$Q_{gs}$	Gate-to-Source Charge	—	22	33	nC	$V_{DS} = -80V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	81	120	nC	$V_{GS} = -10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = -50V$
$t_r$	Rise Time	—	63	—	ns	$I_D = -23A$
$t_{d(off)}$	Turn-Off Delay Time	—	72	—	ns	$R_G = 2.4\Omega$
$t_f$	Fall Time	—	55	—	ns	$V_{GS} = -10V$ ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—	nH	
$C_{iss}$	Input Capacitance	—	2780	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	800	—	pF	$V_{DS} = -25V$
$C_{rss}$	Reverse Transfer Capacitance	—	430	—	pF	$f = 1.0\text{MHz}$ , See Fig. 5

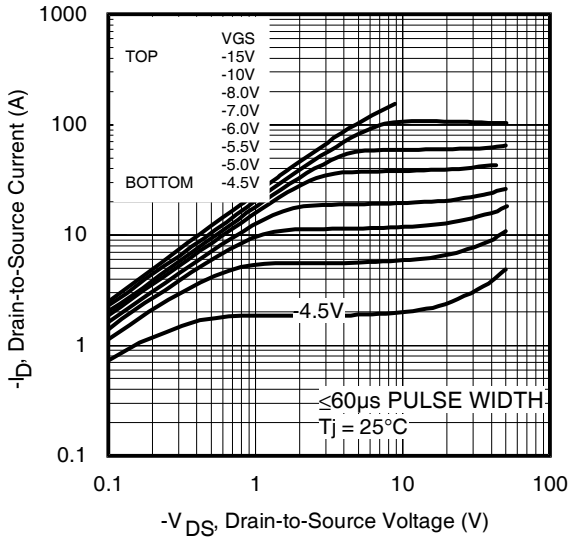
## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-38	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-140	A	
$V_{SD}$	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -23A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	170	260	ns	$T_J = 25^\circ\text{C}, I_F = -23A, V_{DD} = -25V$
$Q_{rr}$	Reverse Recovery Charge	—	1180	1770	nC	$di/dt = -100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

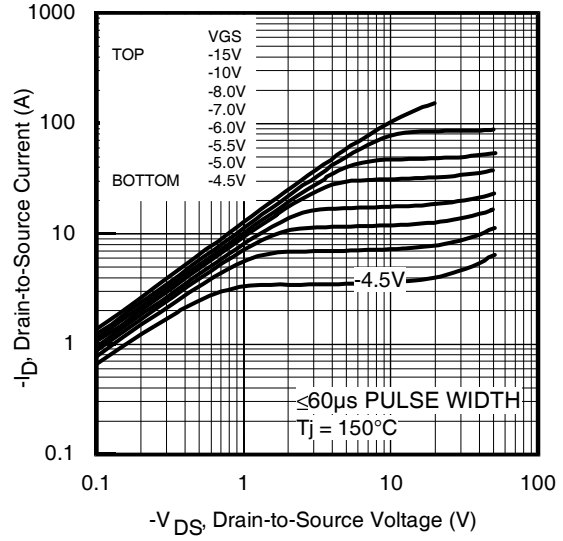
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11)
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.46\text{mH}$   
 $R_G = 25\Omega, I_{AS} = -23A$ . (See Figure 12)
- ③  $I_{SD} \leq -23A, di/dt \leq -650A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$ .

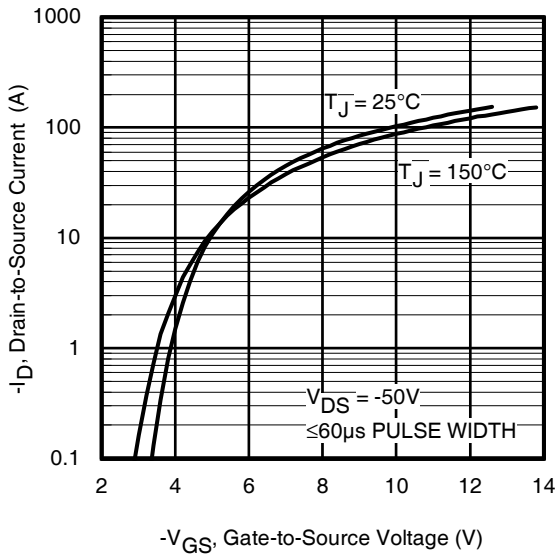
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.



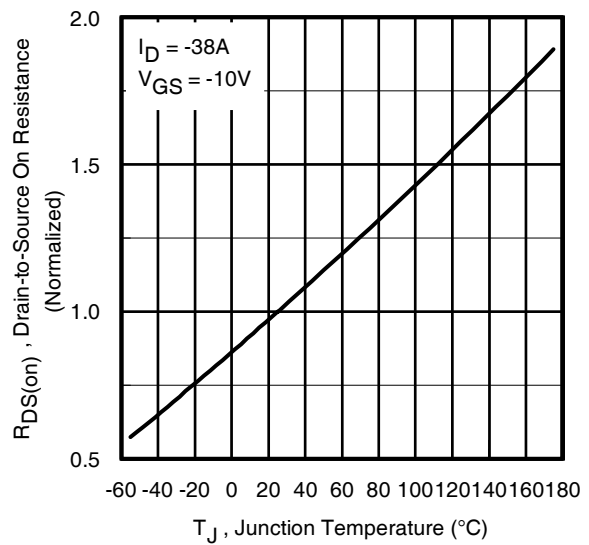
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

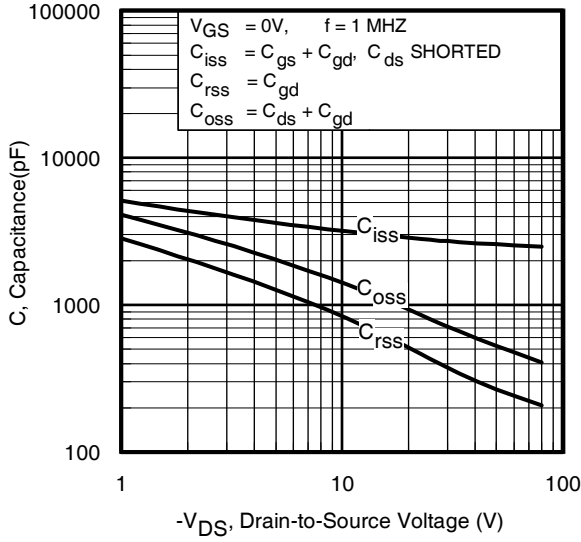


**Fig 3.** Typical Transfer Characteristics

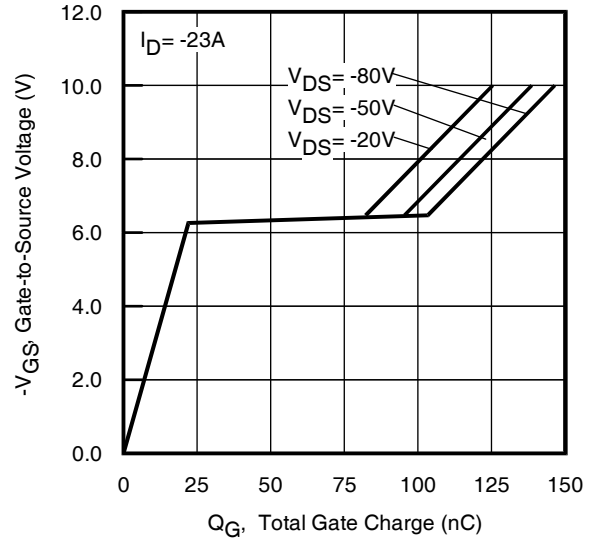


**Fig 4.** Normalized On-Resistance vs. Temperature

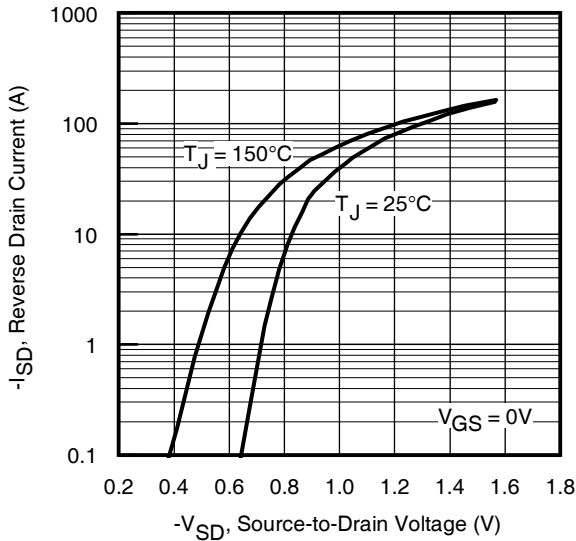
# IRF5210S/LPbF



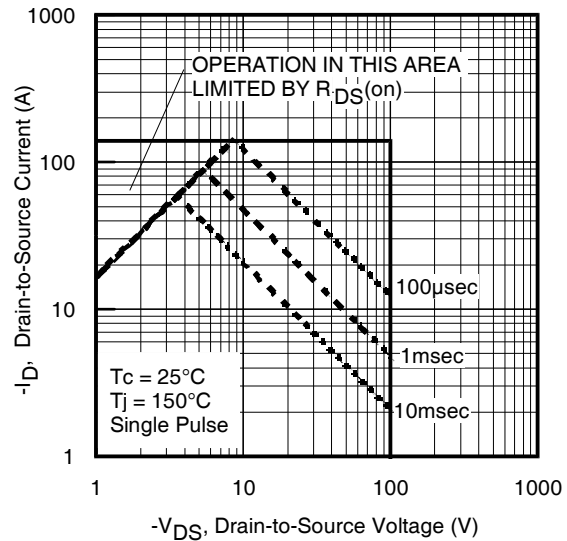
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



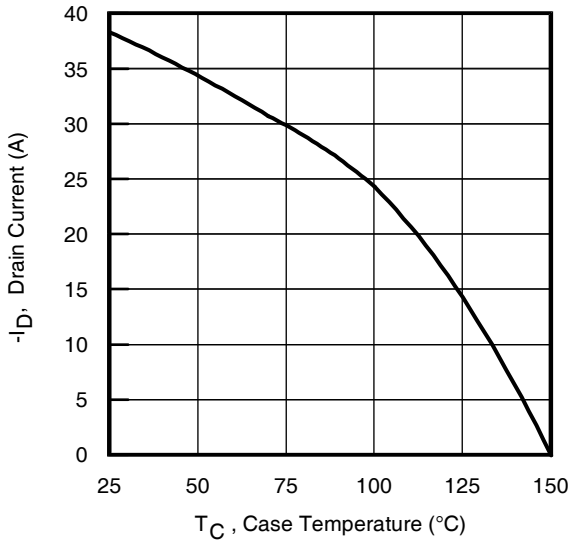
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



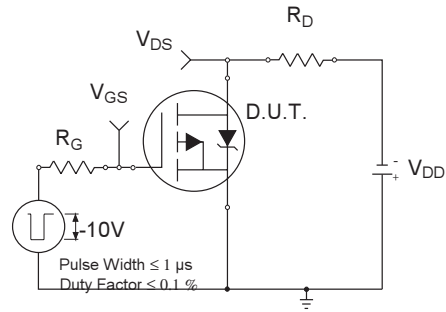
**Fig 7.** Typical Source-Drain Diode Forward Voltage



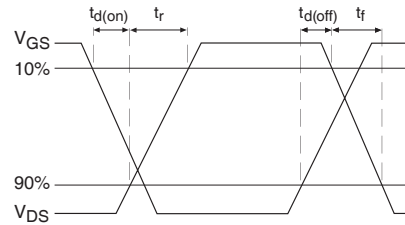
**Fig 8.** Maximum Safe Operating Area



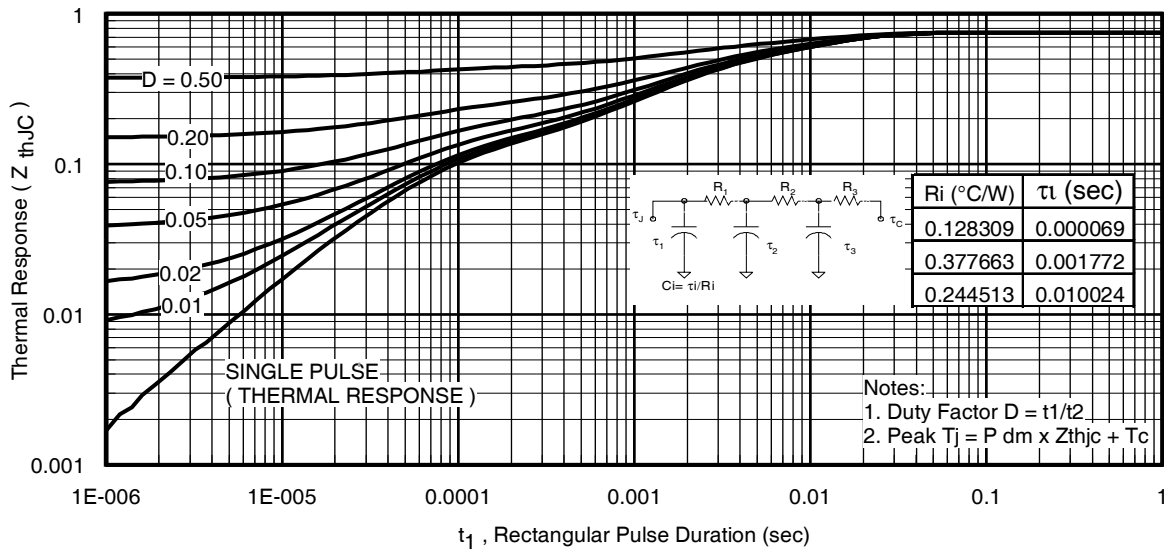
**Fig 9.** Maximum Drain Current vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit

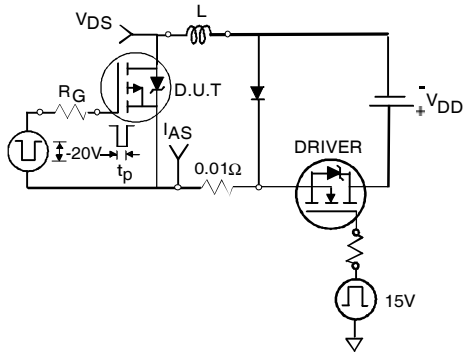


**Fig 10b.** Switching Time Waveforms

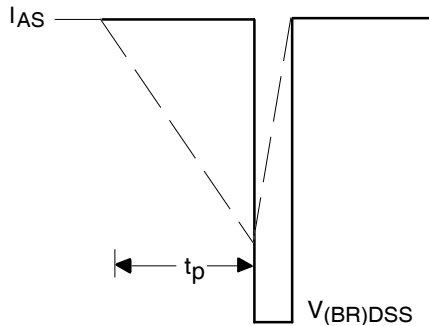


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

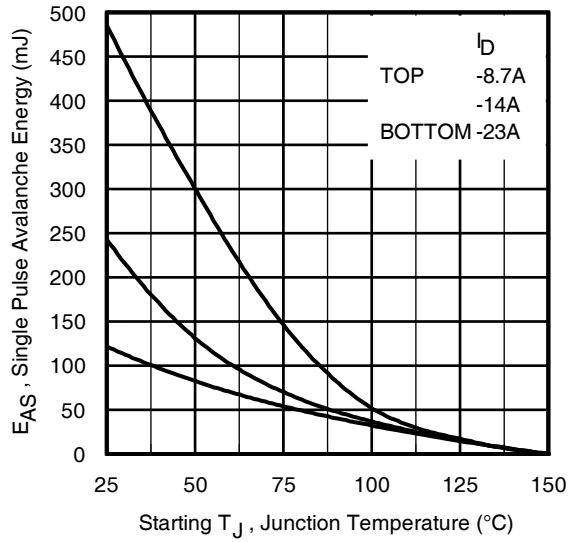
# IRF5210S/LPbF



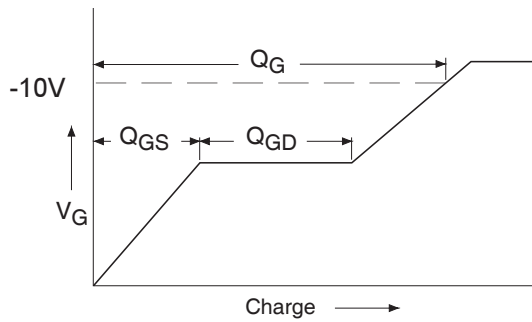
**Fig 12a.** Unclamped Inductive Test Circuit



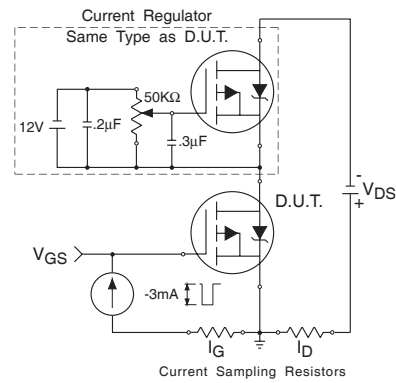
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13.** Maximum Avalanche Energy vs. Drain Current

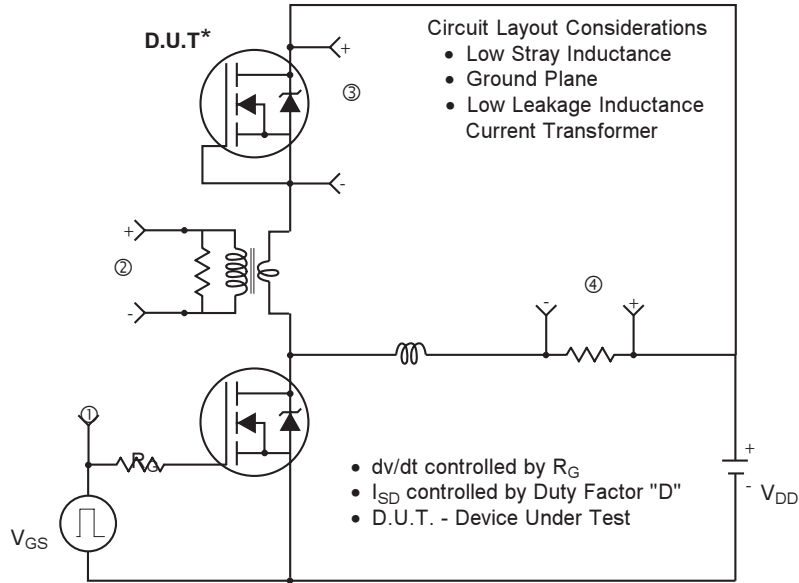


**Fig 14a.** Basic Gate Charge Waveform

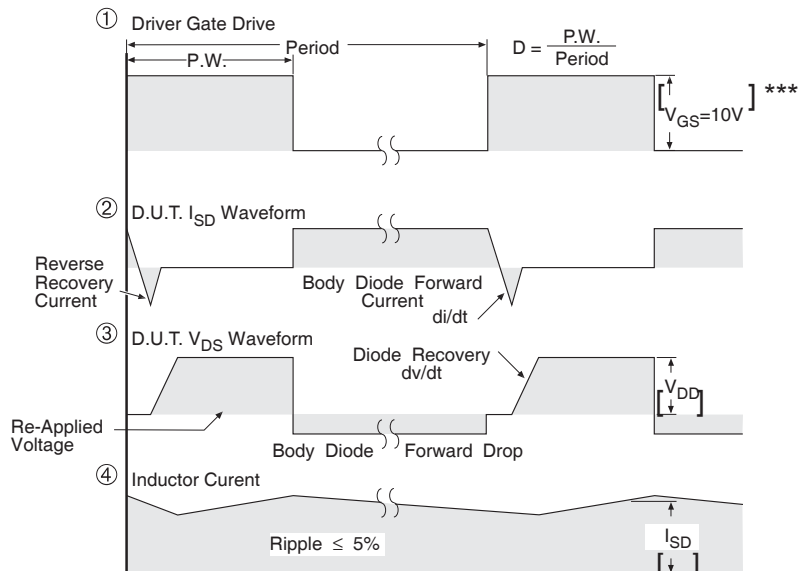


**Fig 14b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity of D.U.T for P-Channel



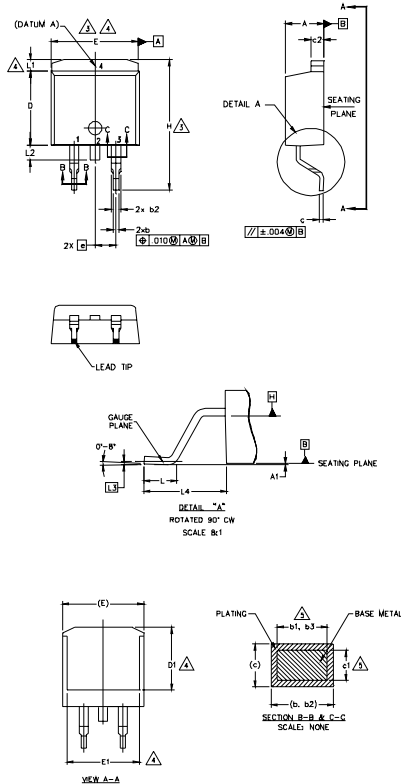
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig 15.** For P-Channel HEXFETS

# IRF5210S/LPbF

## D<sup>2</sup>Pak (TO-263AB) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
  4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
  5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  7. CONTROLLING DIMENSION: INCH.
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	0.35	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	6
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	0.23	5
c2	1.14	1.65	.045	.065	
D	8.36	9.65	.330	.380	3
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		
H	14.61	15.08	.575	.625	
L	1.78	2.79	.070	.110	
L1	-	1.65	-	.066	4
L2	1.27	1.78	-	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	

LEAD ASSIGNMENTS

- HEXFET
- 1.- GATE
  2. 4.- DRAIN
  - 3.- SOURCE

IGBTs, COPACK

- 1.- GATE
2. 4.- COLLECTOR
- 3.- EMITTER

DIODES

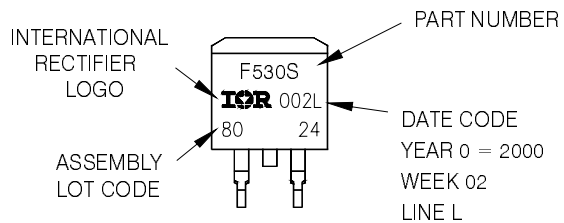
- 1.- ANODE \*
2. 4.- CATHODE
- 3.- ANODE

\* PART DEPENDENT.

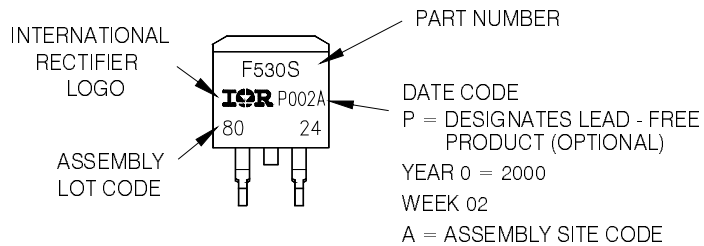
## D<sup>2</sup>Pak (TO-263AB) Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW 02, 2000  
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position indicates "Lead - Free"



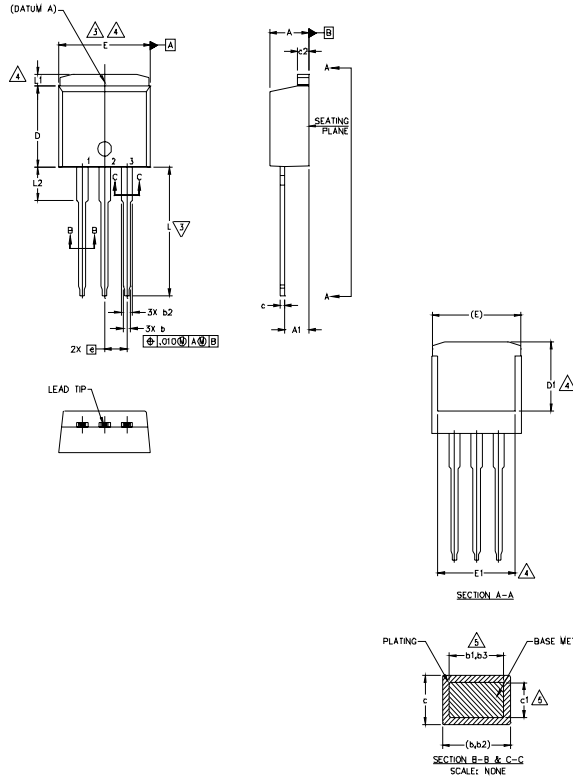
OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## TO-262 Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
  5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  6. CONTROLLING DIMENSION: INCH.
  7. OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.), AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	3.02	.080	.119	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		
L	13.46	14.10	.530	.555	
L1	-	1.65	-	.065	4
L2	3.56	3.71	.140	.146	

**LEAD ASSIGNMENTS**

- HEXFET**
- 1.- GATE
  - 2.- DRAIN
  - 3.- SOURCE
  - 4.- DRAIN

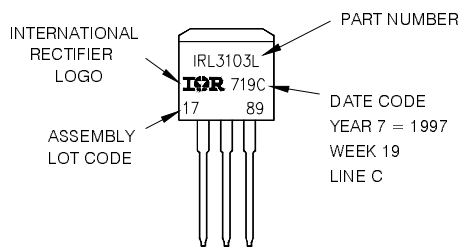
**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

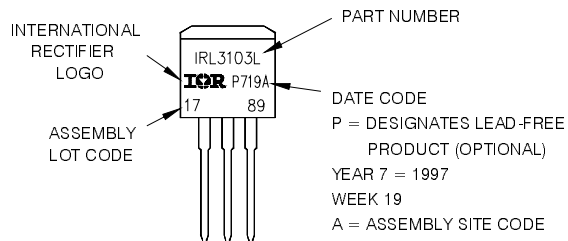
## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE 'C'

Note: "P" in assembly line position indicates "Lead - Free"



OR



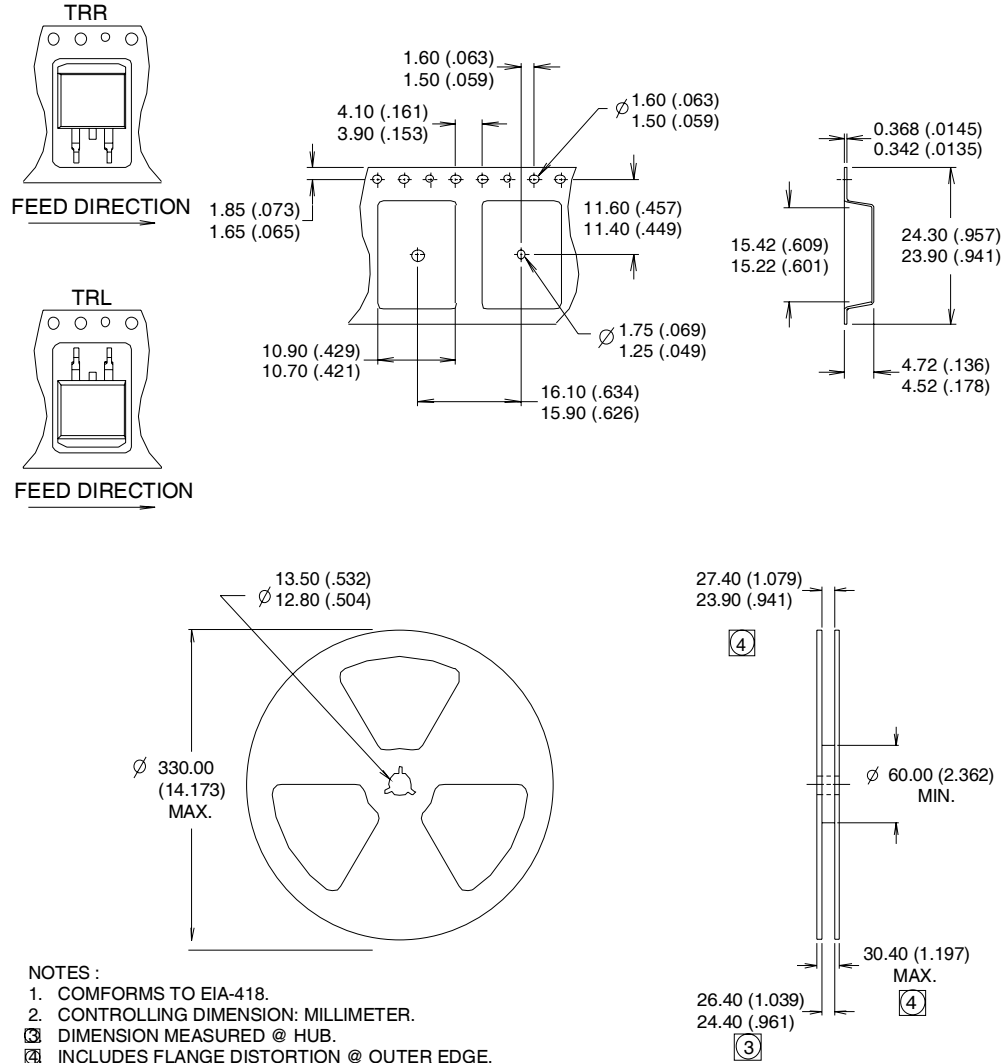
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

# IRF5210S/LPbF

International  
**IR** Rectifier

## D<sup>2</sup>Pak (TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information. 08/09

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

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